# SK 30 DTA



SEMITOP<sup>®</sup> 3

### 3-phase bridge rectifier+ series thyristor

#### SK 30 DTA

Target Data

#### Features

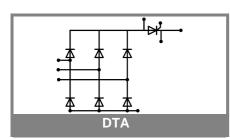
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passivated thyristor chips
- Reverse voltage up to 1600 V
- High surge currents

### **Typical Applications**

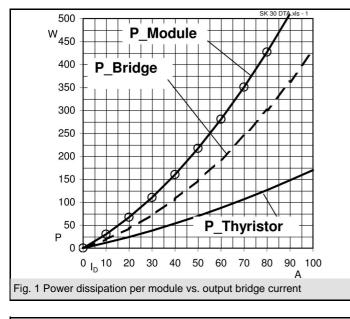
- Soft starters
- Light control
- Temperature control

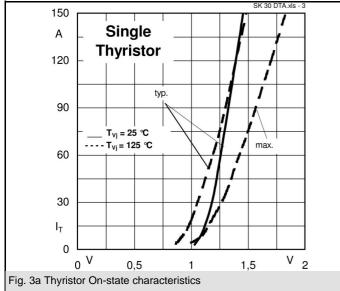
	-	
V <sub>RSM</sub>	V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>D</sub> = 25 A
V	V	(T <sub>s</sub> = 80 °C)
900	800	SK 30 DTA 08
1300	1200	SK 30 DTA 12
1700	1600	SK 30 DTA 16

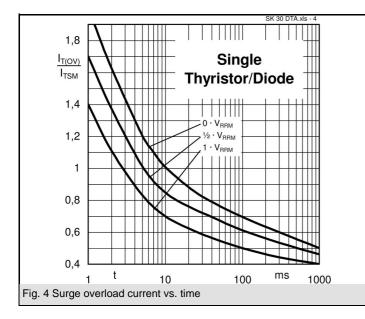
Characteristics		T <sub>s</sub> = 25°C unless otherwise specified		
Symbol	Conditions		Values	Units
I <sub>D</sub>	T <sub>S</sub> = 80°C; Ind. load		25	А
I <sub>TAV</sub>	sin. 180°; T <sub>s</sub> = 25 (80) °C per thyristor		31 (19)	А
I <sub>FAV</sub>	sin. 180°; T <sub>s</sub> = 25 (80) °C per diode		37 (25)	А
I <sub>TSM</sub> /I <sub>FSM</sub>	T <sub>vi</sub> = 25 (125) °C; 10 ms		1000 (900)	Α
l²t	T <sub>vj</sub> = 25 (125) °C; 8,3 10 ms		5000 (4000)	A²s
T <sub>stg</sub>			-40,+125	°C
T <sub>solder</sub>	terminals, 10 s		260	°C
Thyristor				
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C		1000	V/µs
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C; f = f = 50 60 Hz		50	A/µs
t <sub>q</sub>	T <sub>vj</sub> = 125 °C; typ.		80	μs
I <sub>H</sub>	T <sub>vj</sub> = 25 °C; typ. / max.		100 / 200	mA
I <sub>L</sub>	$T_{vj} = 25 \text{ °C}; R_G = 33 \Omega; typ. / max.$		200 / 400	mA
V <sub>T</sub>	T <sub>vi</sub> = 25 °C; (I <sub>T</sub> = 120 A); max.		1,8	V
V <sub>T(TO)</sub>	T <sub>vi</sub> = 125 °C		max. 1	V
r <sub>T</sub>	T <sub>vj</sub> = 125 °C		max. 6	mΩ
I <sub>DD</sub> ; I <sub>RD</sub>	$T_{vj} = 125 \text{ °C}; V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$		max. 8	mA
R <sub>th(j-s)</sub>	Cont. per thyristor		0,8	K/W
T <sub>vj</sub>			- 40 + 125	°C
V <sub>GT</sub>	T <sub>vi</sub> = 25 °C; d.c.		2	V
I <sub>GT</sub>	$T_{vi} = 25 \text{ °C; d.c.}$		100	mA
V <sub>GD</sub>	T <sub>vi</sub> = 125 °C; d.c.		0,25	V
I <sub>GD</sub>	T <sub>vj</sub> = 125 °C; d.c.		5	mA
Diode				
V <sub>F</sub>	T <sub>vj</sub> = 25 °C; (I <sub>F</sub> = 25 A); max.		1,25	V
V <sub>(TO)</sub>	T <sub>vj</sub> = 150 °C		0,8	V
r <sub>T</sub>	T <sub>vj</sub> = 150 °C		4	mΩ
I <sub>RD</sub>	T <sub>vj</sub> = 150 °C; V <sub>RD</sub> = V <sub>RRM</sub>		4	mA
R <sub>th(j-s)</sub>	per diode		1,7	K/W
T <sub>vj</sub>			-40+150	°C
Mechanic	al data			·
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min		3000 (2500)	V
M <sub>1</sub>	mounting torque		2,5	Nm
w			30	g
Case	SEMITOP <sup>®</sup> 3		T 45	

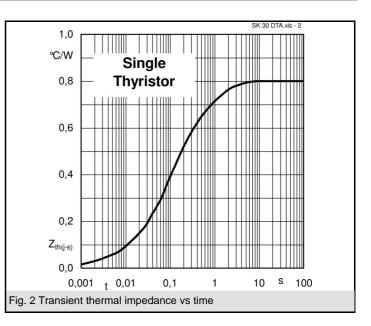


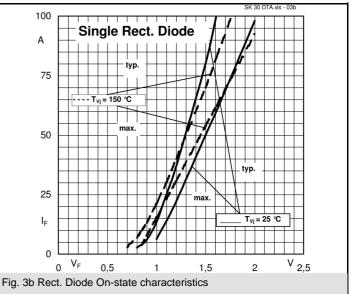
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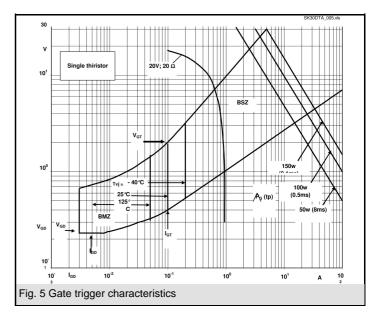






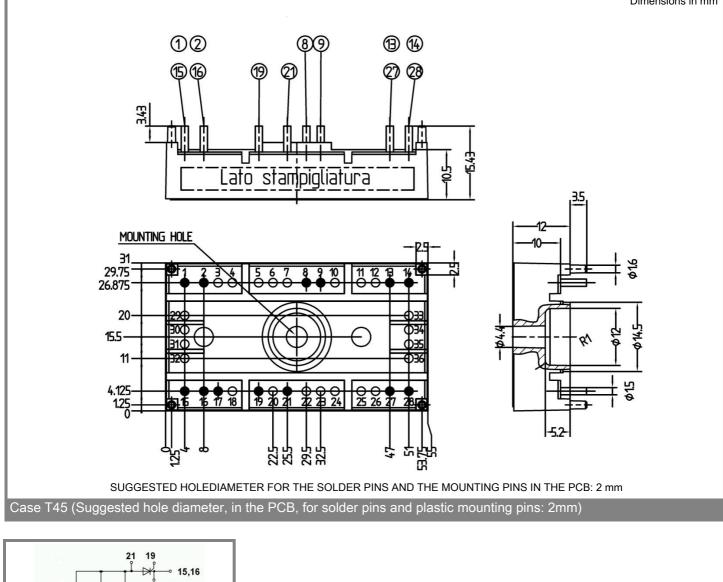


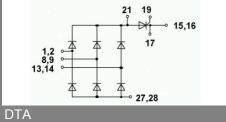




## SK 30 DTA

Dimensions in mm





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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